

Saurav Roy

List of Publications by Year in descending order

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9
papers

358
citations

1039406

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9
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270
citing authors

#	ARTICLE	IF	CITATIONS
1	130 Åm ² In_2O_3 metal semiconductor field effect transistor with low-temperature metalorganic vapor phase epitaxy-regrown ohmic contacts. Applied Physics Express, 2021, 14, 076502.	1.1	39
2	In Situ Dielectric $\text{Al}_2\text{O}_3/\text{In}_2\text{O}_3$ Interfaces Grown Using Metal-Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	2.6	17
3	High-k Oxide Field-Plated Vertical (001) In_2O_3 Schottky Barrier Diode With Baliga's Figure of Merit Over 1 GW/cm ² . IEEE Electron Device Letters, 2021, 42, 1140-1143.	2.2	86
4	Multi-kV Class In_2O_3 -Ga ₂ O ₃ MESFETs With a Lateral Figure of Merit Up to 355 MW/cm ² . IEEE Electron Device Letters, 2021, 42, 1272-1275.	2.2	50
5	Growth and characterization of metalorganic vapor-phase epitaxy-grown $\text{In}_2(\text{Al}_x)$ Tj ETQq1 1 0.784314 rgBT /Overlock 10 channels. Applied Physics Express, 2021, 14, 025501.	1.1	40
6	Low temperature homoepitaxy of (010) In_2O_3 -Ga ₂ O ₃ by metalorganic vapor phase epitaxy: Expanding the growth window. Applied Physics Letters, 2020, 117, .	1.5	56
7	Design of a In_2O_3 Schottky Barrier Diode With p-Type III-Nitride Guard Ring for Enhanced Breakdown. IEEE Transactions on Electron Devices, 2020, 67, 4842-4848.	1.6	21
8	Delta-doped In_2O_3 films with narrow FWHM grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2020, 117, .	1.5	17
9	Schottky Barrier Height Engineering in In_2O_3 -Ga ₂ O ₃ Using SiO ₂ Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	1.2	32